

#### 175°C P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

## **Product Summary**

BV <sub>DSS</sub>	RDS(ON) Max	I <sub>D</sub> Tc = +25°C
-40V	10mΩ @V <sub>GS</sub> = -10V	-50A
-40 V	14mΩ @Vgs = -4.5V	-40A

## **Features and Benefits**

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switch (UIS) Test in Production Low On-Resistance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DIODES™ DMPH4015SPSQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

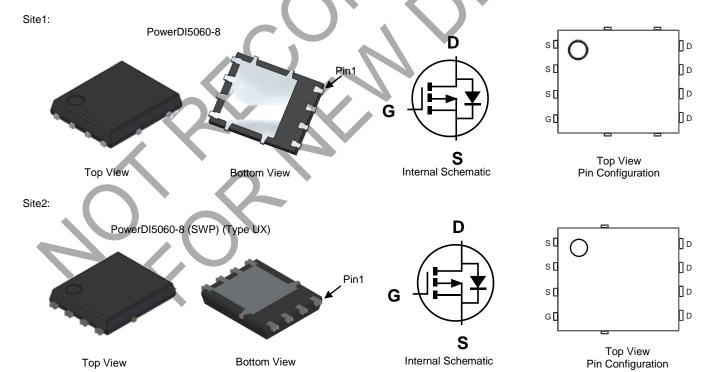
## **Description and Applications**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Reverse polarity protections
- **BLDC** motor controls
- Power management functions

## **Mechanical Data**

- Package: PowerDI®5060-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish 100% Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)



Notes: 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + CI) and <1000ppm antimony compounds.

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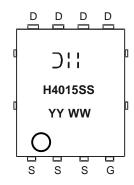
## Ordering Information (Note 4)

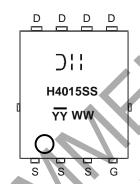
Part Number	Pankaga	Packing		
Fait Number	Package	Qty.	Carrier	
DMPH4015SPSQ	PowerDI5060-8	2,500	Reel	
DMPH4015SPSQ	PowerDI5060-8 (SWP) (Type UX)	2,500	Reel	

Note:

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**





);; = Manufacturer's Marking
H4015SS = Product Type Marking Code
YYWW or YYWW = Date Code Marking
YY or YY = Year (ex: 22 = 2022)
WW = Week (01 to 53)

## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			VDSS	-40	V
Gate-Source Voltage			V <sub>GSS</sub>	±25	V
Continuous Drain Current V <sub>GS</sub> = -10V (Note 7)	Steady State	Tc = +25°C Tc = +100°C	ID	-50 -35	А
Continuous Drain Current V <sub>GS</sub> = -10V (Note 6)	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +100°C	I <sub>D</sub>	-12.0 -9.0	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	-100	Α
Maximum Body Diode Continuous Current (Note 7)			Is	-50	Α
Avalanche Current L = 1mH			las	-22	А
Avalanche Energy L = 1mH			E <sub>AS</sub>	260	mJ

## Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25$ °C	PD	1.5	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	98	°C/W
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	PD	2.6	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Reja	57	°C/W
Thermal Resistance, Junction to Case (Note 7)		R <sub>0</sub> JC	0.9	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +175	°C

Notes

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
- 7. Thermal resistance from junction to soldering point (on the exposed drain pad).



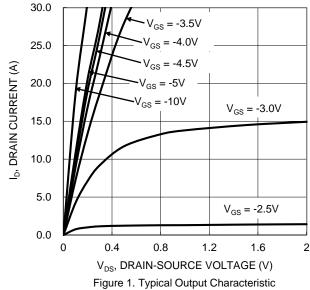
# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BVDSS	-40	_	_	V	V <sub>G</sub> S = 0V, I <sub>D</sub> = -250µA	
Zero Gate Voltage Drain Current	IDSS	_	_	-1	μA	V <sub>DS</sub> = -40V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 25V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)	•			•	•		
Gate Threshold Voltage	Vgs(TH)	-1.5	-2	-2.5	V	$V_{DS} = V_{GS}$ , $I_D = -250\mu A$	
Static Drain-Source On-Resistance	D	_	8	10	mΩ	$V_{GS} = -10V, I_{D} = -9.8A$	
Static Diain-Source On-Resistance	RDS(ON)	_	11	14	1117.5	$V_{GS} = -4.5V, I_{D} = -9.8A$	
Diode Forward Voltage	$V_{SD}$	_	-0.7	-1	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1A	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss	1	4234			201/1/ 01/	
Output Capacitance	Coss	l	1036	_	pF	$V_{DS} = -20V, V_{GS} = 0V,$ f = 1MHz	
Reverse Transfer Capacitance	Crss		526	_		1 = 110112	
Gate Resistance	Rg	1	7.8		Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Qg		42.7	-			
Total Gate Charge (V <sub>GS</sub> = -10V)	Qg		91		nC	$V_{DS} = -20V$ ,	
Gate-Source Charge	Qgs	_	14.2		lic	$I_D = -9.8A$	
Gate-Drain Charge	Qgd		13.5				
Turn-On Delay Time	t <sub>D(ON)</sub>	_	13.2			<b>*</b>	
Turn-On Rise Time	t <sub>R</sub>	_	10		no	$V_{GS} = -10V, V_{DD} = -20V,$	
Turn-Off Delay Time	tD(OFF)	-	303	<b>V</b> -	ns	$R_G = 6\Omega$ , $I_D = -1A$	
Turn-Off Fall Time	tF	_	138				
Reverse Recovery Time	trr	H	26	-/	ns	I <sub>F</sub> = -9.8A, di/dt = -100A/μs	
Reverse Recovery Charge	Q <sub>RR</sub>	-	20	4	nC	I <sub>F</sub> = -9.8A, di/dt = -100A/μs	

8. Short duration pulse test used to minimize self-heating effect.9. Guaranteed by design. Not subject to product testing. Notes:







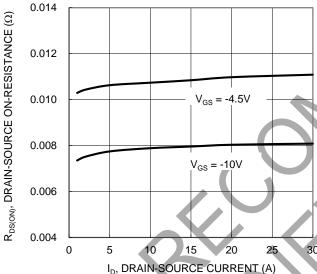


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

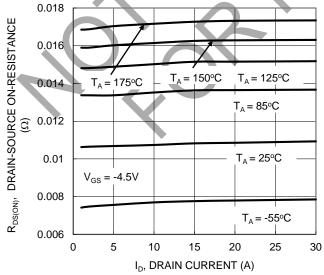


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

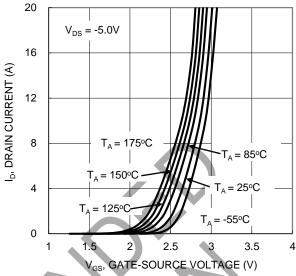


Figure 2. Typical Transfer Characteristic

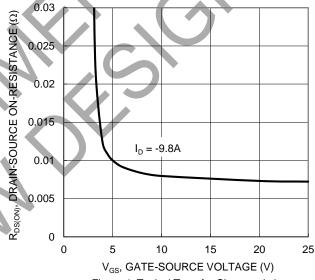


Figure 4. Typical Transfer Characteristic

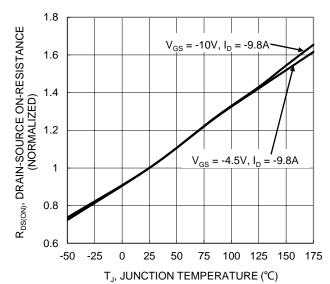


Figure 6. On-Resistance Variation with Temperature



 $I_D = -1mA$ 



30

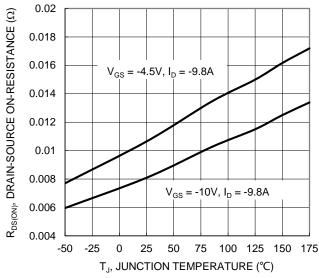
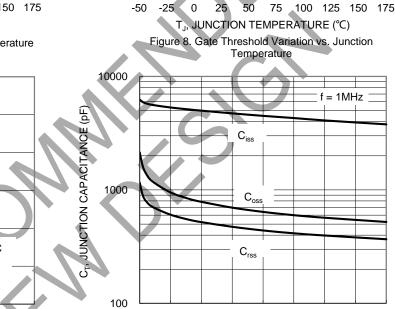


Figure 7. On-Resistance Variation with Temperature



 $I_{D} = -250 \mu A$ 

2.2

2

1.8

1.6

1.4

1.2

0

5

10

15

20

V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V)

Figure 10. Typical Junction Capacitance

25

30

35

40

 $V_{GS(TH)},\; GATE\; THRESHOLD\; VOLTAGE\; (V)$ 

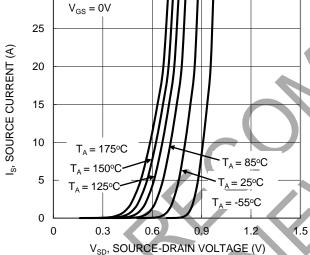


Figure 9. Diode Forward Voltage vs. Current

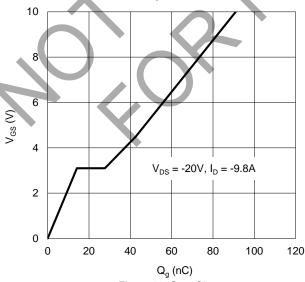


Figure 11. Gate Charge

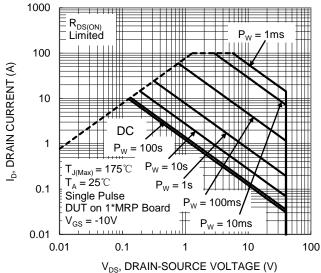


Figure 12. SOA, Safe Operation Area



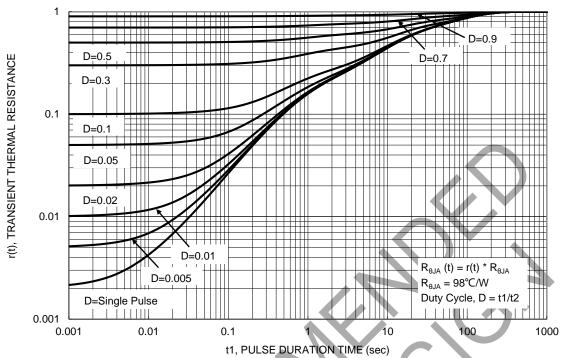


Figure 13. Transient Thermal Resistance

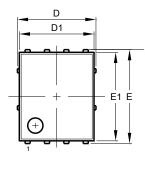


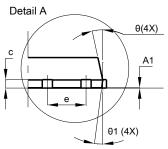
## **Package Outline Dimensions**

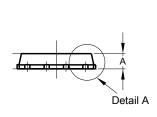
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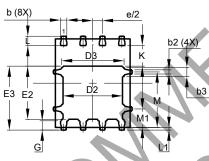
#### Site1:

### PowerDI5060-8





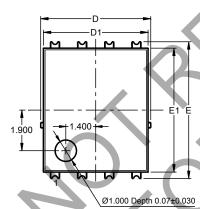


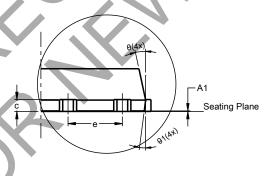


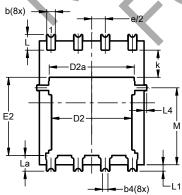
PowerDI5060-8					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
<b>A</b> 1	0.00	0.05	-		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3 _	0.40	0.80	0.60		
C	0.230	0.330	0.277		
D		5.15 BSC	;		
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90	4.30	4.10		
E	•	6.15 BSC	;		
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99	4.39	4.19		
е		1.27 BSC	;		
G	0.51	0.71	0.61		
K	0.51	_	-		
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
M	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
Θ	10°	12°	11°		
Θ1	6°	8°	7°		
All Dimensions in mm					

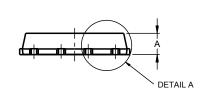
#### Site2:

# PowerDI5060-8 (SWP) (Type UX)









DETAIL A

PowerDI5060-8 (SWP) (Type UX)				
Dim	Min	Max	Тур	
Α	0.90	1.10	1.00	
A1	0	0.05		
b	0.30	0.50	0.41	
b2	0.20	0.35	0.25	
b4		0.25REF		
С	0.230	0.330	0.277	
D	Ę	5.15 BSC	;	
D1	4.70	5.10	4.90	
D2	3.56	3.96	3.76	
D2a	3.78	4.18	3.98	
E	(	6.40 BSC	;	
E1	5.60	6.00	5.80	
E2	3.46	3.86	3.66	
E2a	4.195	4.595	4.395	
е		1.27BSC		
k	1.05			
L	0.635	0.835	0.735	
La	0.635	0.835	0.735	
L1	0.200	0.400	0.300	
L1a	0.050REF			
L4	0.025	0.225	0.125	
M	3.205	4.005	3.605	
θ	10°	12°	11°	
θ1	6°	8°	7°	
All Dimensions in mm				

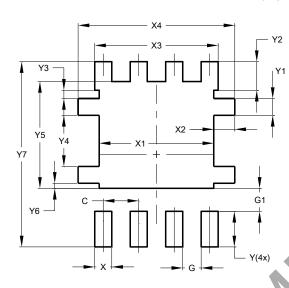


## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### Site1:

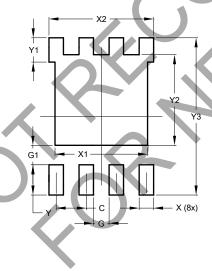
#### PowerDI5060-8



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
Х3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

#### Site2:

# PowerDI5060-8 (SWP) (Type UX)



Dimensions	Value (in mm)	
С	1.270	
G	0.660	
G1	0.820	
X	0.610	
X1	4.100	
X2	4.420	
Y	1.270	
Y1	1.020	
Y2	3.810	
Y3	6.610	



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